

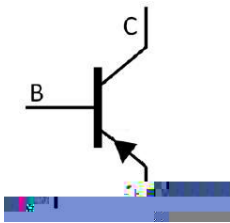
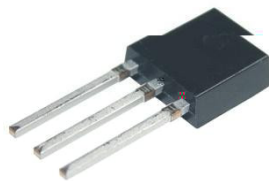
Rev.E Mar.-2016

TO-251 PNP Silicon PNP transistor in a TO-251 Plastic Package.

, 2SD880I

Low collector saturation voltage, collector power dissipation, complementary to 2SD880I.

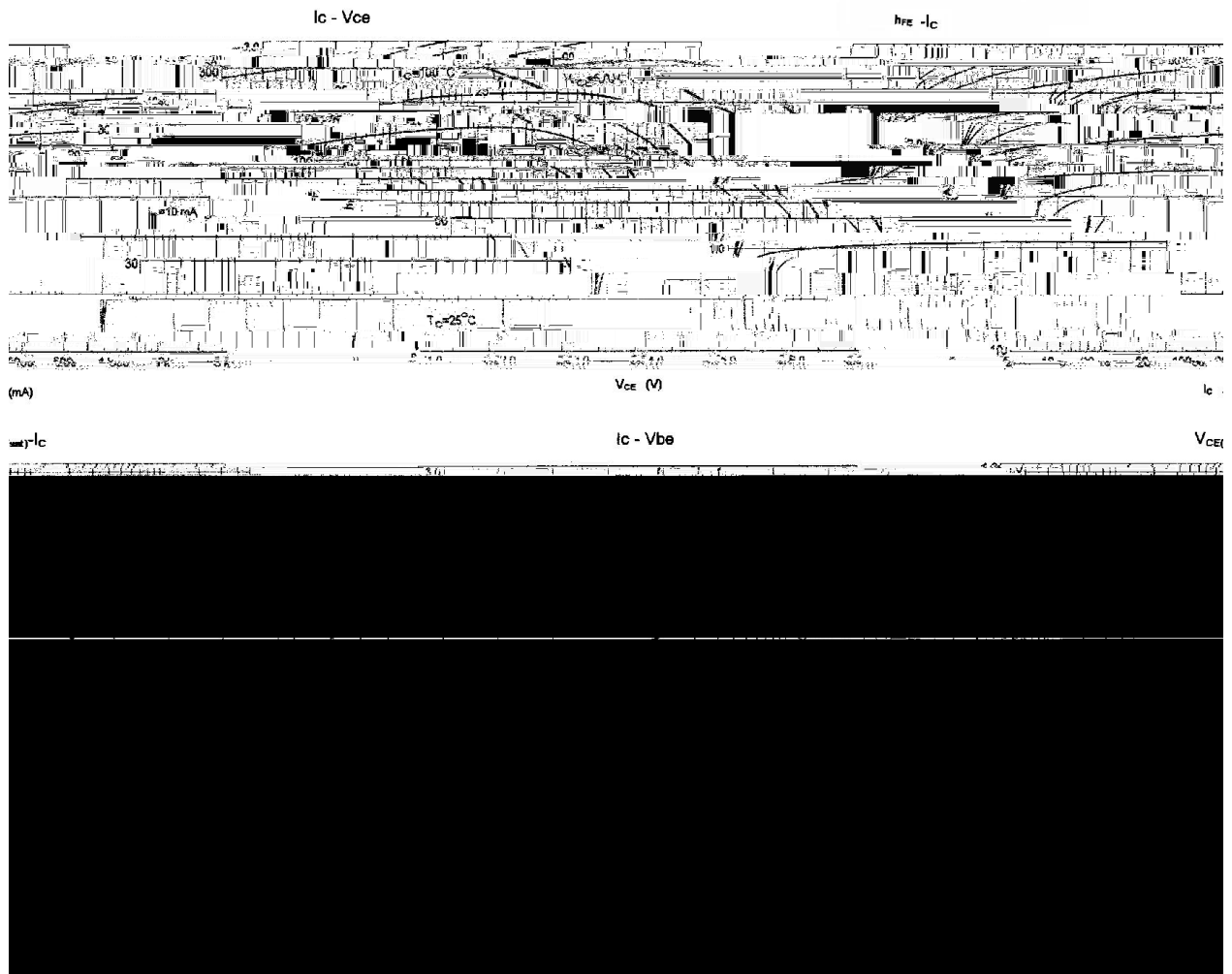
Audio frequency power amplifier applications.

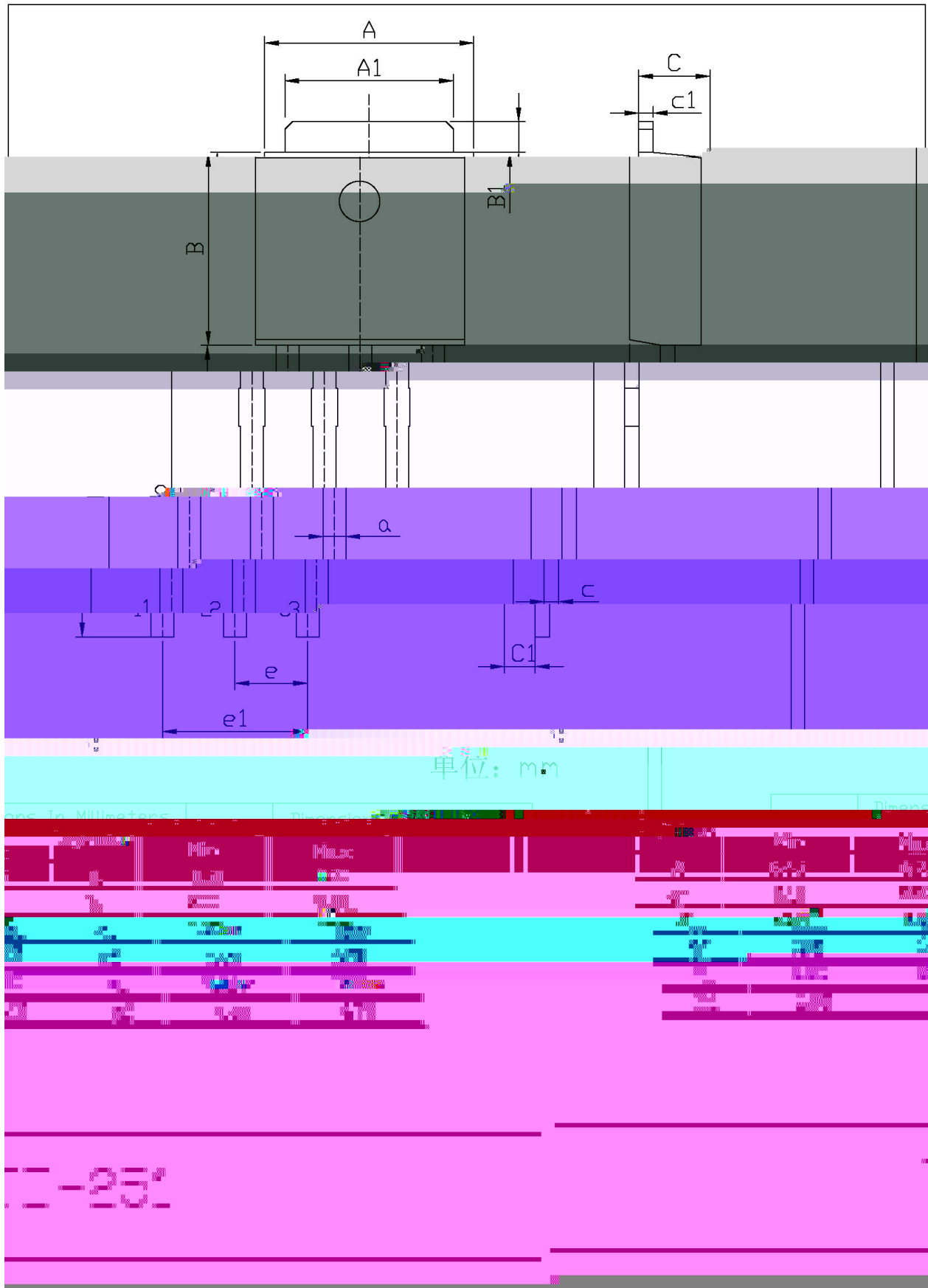


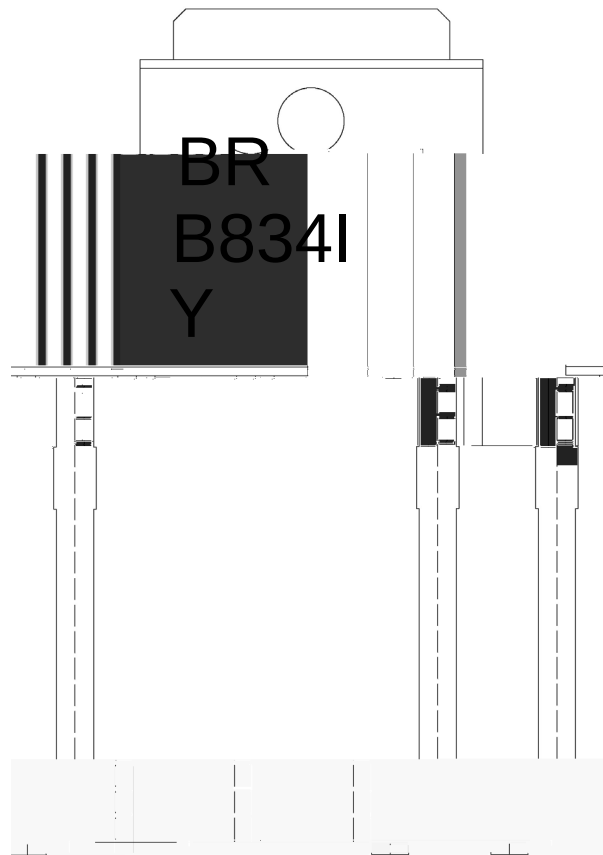
PIN1 Base PIN 2 Collector PIN 3 Emitter

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	I_C	-3.0	A
Base Current - Continuous	I_B	-0.5	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -50mA$ $I_B = 0$	-60			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -60V$ $I_E = 0$			-100	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -7.0V$ $I_C = 0$			-100	A
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -5.0V$ $I_C = -0.5A$	60		300	
	$h_{FE(2)}$	$V_{CE} = -5.0V$ $I_C = -3.0A$	20			
Collector to Emitter Saturation Voltage Base to Emitter Voat)	$V_{CE(sat)}$	$I_C = -3.0A$ $I_B = -0.3A$		-0.5	-1.0	V







BR

B834I

Y: h_{FE}

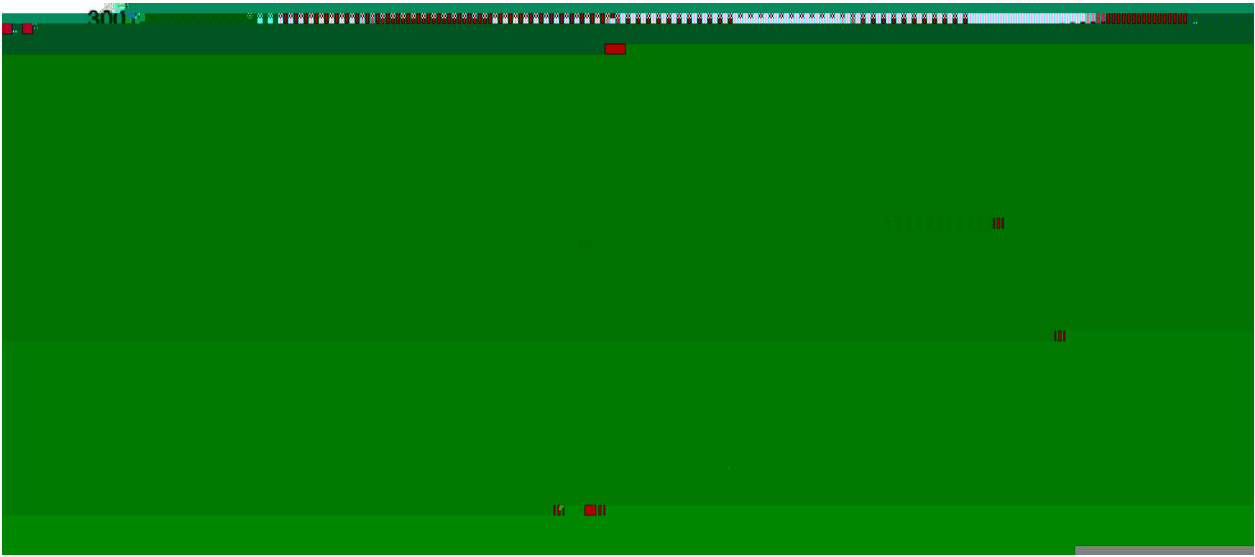
Note:

BR: Company Code

B834I: Product Type.

Y: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

255±5

5±0.5sec;

2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3

2 10

/sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱